# **Configurable Multifunction Gate**

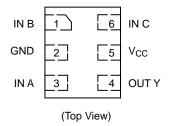
The NLX1G57 MiniGate<sup>™</sup> is an advanced high-speed CMOS multifunction gate. The device allows the user to choose logic functions AND, OR, NAND, NOR, XNOR, INVERT and BUFFER. The device has Schmitt-trigger inputs, thereby enhancing noise immunity.

The NLX1G57 input and output structures provide protection when voltages up to 7.0 V are applied, regardless of the supply voltage.

#### **Features**

- High Speed:  $t_{PD} = 3.2 \text{ ns (Typ)} @ V_{CC} = 5.0 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 1 \mu A$  (Maximum) at  $T_A = 25^{\circ}C$
- Power Down Protection Provided on inputs
- Balanced Propagation Delays
- Overvoltage Tolerant (OVT) Input and Output Pins
- Ultra-Small Package
- This is a Pb-Free Device

## **PIN ASSIGNMENTS**





## ON Semiconductor®

www.onsemi.com

## MARKING DIAGRAMS



UDFN6 1.0 x 1.0 CASE 517BX



P = Specific Device Code

M = Date Code

#### **ORDERING INFORMATION**

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

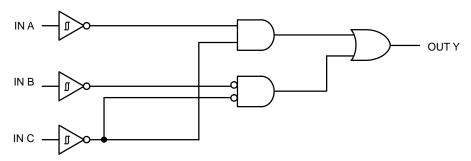


Figure 1. Function Diagram

## **PIN ASSIGNMENT**

1	IN B
2	GND
3	IN A
4	OUT Y
5	V <sub>CC</sub>
6	IN C

# **FUNCTION TABLE\***

	Input						
Α	В	С	Υ				
L	L	L	Н				
L	L	Н	L				
L	Н	L	Н				
L	Н	Н	Н				
Н	L	L	L				
Н	L	Н	L				
Н	Н	L	L				
Н	Н	Н	Н				

<sup>\*</sup>To select a logic function, please refer to "Logic Configurations section".

## **LOGIC CONFIGURATIONS**

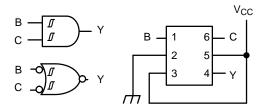


Figure 2. 2-Input AND (When A = "H")

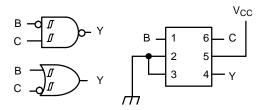


Figure 3. 2-Input NAND with input B inverted (When A = "L")

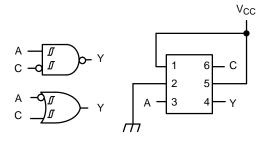


Figure 4. 2-Input NAND with Input C Inverted (When B = "H")

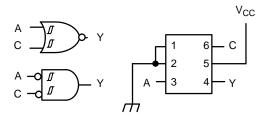


Figure 5. 2-Input NOR (When B = "L")

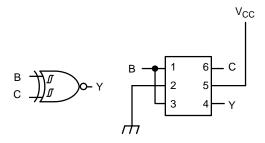


Figure 6. 2-Input XNOR (When A = B)

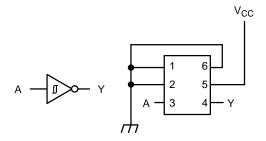


Figure 7. Inverter (When B = C = "L")

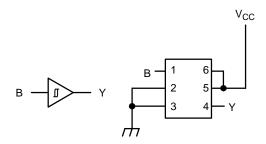


Figure 8. Buffer (When A = "L" and C = "H")

## **MAXIMUM RATINGS**

Symbol	Parameter		Value	Unit
V <sub>CC</sub>	DC Supply Voltage		-0.5 to +7.0	V
V <sub>IN</sub>	DC Input Voltage		-0.5 to +7.0	V
V <sub>OUT</sub>	DC Output Voltage		-0.5 to +7.0	V
I <sub>IK</sub>	DC Input Diode Current	V <sub>IN</sub> < GND	-50	mA
l <sub>ok</sub>	DC Output Diode Current	V <sub>OUT</sub> < GND	-50	mA
Io	DC Output Source/Sink Current		±50	mA
Icc	DC Supply Current Per Supply Pin		±100	mA
I <sub>GND</sub>	DC Ground Current per Ground Pin		±100	mA
T <sub>STG</sub>	Storage Temperature Range		-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds		260	°C
TJ	Junction Temperature Under Bias		150	°C
MSL	Moisture Sensitivity		Level 1	
F <sub>R</sub>	Flammability Rating Oxygen	Index: 28 to 34	UL 94 V-0 @ 0.125 in	
V <sub>ESD</sub>	Machi	dy Model (Note 2) ne Model (Note 3) ce Model (Note 4)	>2000 >200 N/A	V
I <sub>LATCHUP</sub>	Latchup Performance Above V <sub>CC</sub> and Below GND at	125°C (Note 5)	±500	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. Measured with minimum pad spacing on an FR4 board, using 10 mm-by-1 inch, 2 ounce copper trace no air flow.
- 2. Tested to EIA/JESD22-A114-A.
- 3. Tested to EIA/JESD22-A115-A.
- 4. Tested to JESD22-C101-A.
- 5. Tested to EIA/JESD78.

## **RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Min	Max	Unit	
V <sub>CC</sub>	Positive DC Supply Voltage		1.65	5.5	V
V <sub>IN</sub>	Digital Input Voltage	0	5.5	V	
V <sub>OUT</sub>	Output Voltage	0	5.5	V	
T <sub>A</sub>	Operating Free–Air Temperature	-55	+125	°C	
Δt/ΔV	Input Transition Rise or Fall Rate	$V_{CC} = 2.5 \text{ V} \pm 0.2 \text{ V}$ $V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$ $V_{CC} = 5.0 \text{ V} \pm 0.5 \text{ V}$	0 0 0	No Limit No Limit No Limit	nS/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

## DC ELECTRICAL CHARACTERISTICS

			V <sub>CC</sub>	7	Γ <sub>A</sub> = 25°	С	T <sub>A</sub> ≤	+85°C	T <sub>A</sub> = -{ +12	55°C to 5°C	
Symbol	Parameter	Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>T+</sub>	Positive		1.65	0.79		1.16		1.16		1.16	V
	Threshold Voltage		2.3	1.11		1.56		1.56		1.56	
			3.0	1.5		1.87		1.87		1.87	
			4.5	2.16		2.74		2.74		2.74	
			5.5	2.61		3.33		3.33		3.33	
$V_{T-}$	Negative		1.65	0.35		0.62	0.35		0.35		V
	Threshold Voltage		2.3	0.58		0.87	0.58		0.58		1
	voltage		3.0	0.84		1.19	0.84		0.84		1
			4.5	1.41		1.9	1.41		1.41		
			5.5	1.78		2.29	1.78		1.78		1
V <sub>H</sub>	Hysteresis		1.65	0.30		0.62	0.30	0.62	0.30	0.62	V
	Voltage		2.3	0.40		0.8	0.40	0.8	0.40	0.8	1
			3.0	0.53		0.87	0.53	0.87	0.53	0.87	1
			4.5	0.71		1.04	0.71	1.04	0.71	1.04	1
			5.5	0.8		1.2	0.8	1.2	0.8	1.2	1
V <sub>OH</sub>	Minimum High-Level	$V_{IN} = V_{T-MIN} \text{ or } V_{T+MAX}$ $I_{OH} = -50  \mu\text{A}$	1.65 – 5.5	V <sub>CC</sub> - 0.1			V <sub>CC</sub> - 0.1		V <sub>CC</sub> - 0.1		V
	Output Voltage	$V_{IN} = V_{T-MIN}$ or $V_{T+MAX}$									
		$I_{OH} = -4 \text{ mA}$	1.65	1.2			1.2		1.2		
		$I_{OH} = -8 \text{ mA}$	2.3	1.9			1.9		1.9		
		I <sub>OH</sub> = -16 mA	3.0	2.4			2.4		2.4		
		I <sub>OH</sub> = -24 mA	3.0	2.3			2.3		2.3		
		I <sub>OH</sub> = -32 mA	4.5	3.8			3.8		3.8		
V <sub>OL</sub>	Maximum Low-Level	$V_{IN} = V_{T-MIN} \text{ or } V_{T+MAX}$ $I_{OL} = 50  \mu\text{A}$	1.65 – 5.5			0.1		0.1		0.1	V
	Output Voltage	$V_{IN} = V_{T-MIN}$ or $V_{T+MAX}$									
		I <sub>OL</sub> = 4 mA	1.65			0.45		0.45		0.45	
		I <sub>OL</sub> = 8 mA	2.3			0.3		0.3		0.3	
		I <sub>OL</sub> = 16 mA	3.0			0.4		0.4		0.4	
		I <sub>OL</sub> = 24 mA	3.0			0.55		0.55		0.55	1
		I <sub>OL</sub> = 32 mA	4.5			0.55		0.55		0.55	1
I <sub>IN</sub>	Input Leakage Current	0 ≤ V <sub>IN</sub> ≤ 5.5 V	0 to 5.5			± 0.1		±1.0		±1.0	μΑ
I <sub>CC</sub>	Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			1.0		10		10	μΑ

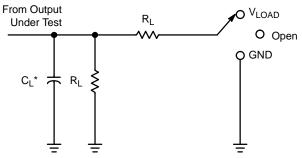
Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$ )

				1	Γ <sub>A</sub> = 25°0		T <sub>A</sub> ≤	+85°C	T <sub>A</sub> = - to +1	-55°C 25°C	
Symbol	Parameter	V <sub>CC</sub> (V)	Test Condition	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> ,	Propagation Delay,	1.65 – 1.95		2.0	8.5	14.4	2.0	14.4	2.0	14.4	ns
t <sub>PHL</sub>	Any Input to Output Y (See Test Circuit)	2.3 – 2.7			4.9	9.0		9.1		9.5	
		3.0 – 3.6			3.8	7.8		8.2		8.3	
		4.5 – 5.5			3.2	7.3		7.4		7.4	
C <sub>IN</sub>	Input Capacitance				3.5						pF
C <sub>PD</sub>	Power Dissipation Capacitance (Note 6)	5.0	f = 10 MHz		22						pF

<sup>6.</sup> C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the dynamic operating current consumption without load. Average operating current can be obtained by the equation I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>. C<sub>PD</sub> is used to determine the no–load dynamic power consumption: P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

## **TEST CIRCUIT AND VOLTAGE WAVEFORMS**



Test	<b>S</b> 1
t <sub>PLH</sub> /t <sub>PHL</sub>	Open
t <sub>PLZ</sub> /t <sub>PZL</sub>	$V_{LOAD}$
t <sub>PHZ</sub> /t <sub>PZH</sub>	GND

Figure 9. Load Circuit

	Inputs						
V <sub>CC</sub>	VI	t <sub>r</sub> /t <sub>f</sub>	V <sub>M</sub>	$V_{LOAD}$	CL	$R_{L}$	$V_\Delta$
1.8 V ± 0.15 V	V <sub>CC</sub>	≤ 2 ns	V <sub>CC</sub> /2	2 x V <sub>CC</sub>	30 pF	1 kΩ	0.15 V
2.5 V ± 0.2 V	V <sub>CC</sub>	≤ 2 ns	V <sub>CC</sub> /2	2 x V <sub>CC</sub>	30 pF	500 Ω	0.15 V
3.3 V ± 0.3 V	3 V	≤ 2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5.5 V ± 0.5 V	V <sub>CC</sub>	≤ 2.5 ns	V <sub>CC</sub> /2	2 x V <sub>CC</sub>	50 pF	500 Ω	0.3 V

 $<sup>^{\</sup>star}C_{L}$  includes probes and jig capacitance.

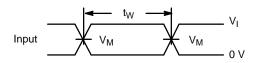


Figure 10. Voltage Waveforms Pulse Duration

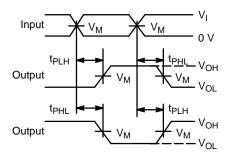


Figure 12. Voltage Waveforms Propagation Delay Times Inverting and Noninverting Outputs

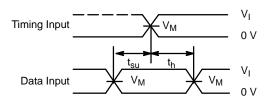


Figure 11. Voltage Waveforms Setup and Hold Times

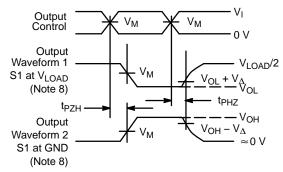


Figure 13. Voltage Waveforms Enable and Disable Times Low- and High-Level Enabling

- 7. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control.
- 8. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control
- 9. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz,  $Z_{\Omega} = 50 \Omega$ .
- 10. The outputs are measured one at a time, with one transition per measurement.
- 11. All parameters are waveforms are not applicable to all devices.

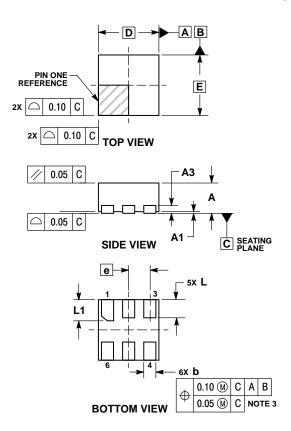
## **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NLX1G57CMUTCG	UDFN6, 1.0 x 1.0, 0.35P (Pb-Free)	3000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### PACKAGE DIMENSIONS

## UDFN6 1.0x1.0. 0.35P CASE 517BX **ISSUE O**

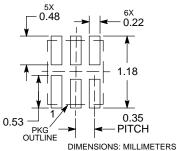


#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.
- DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.20 MM FROM TERMINAL TIP. PACKAGE DIMENSIONS EXCLUSIVE OF
- BURRS AND MOLD FLASH.

	MILLIMETERS						
DIM	MIN	MAX					
Α	0.45	0.55					
A1	0.00	0.05					
A3	0.13 REF						
b	0.12	0.22					
D	1.00	BSC					
E	1.00 BSC						
е	0.35 BSC						
L	0.25	0.35					
L1	0.30	0.40					

## **RECOMMENDED** SOLDERING FOOTPRINT\*



\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

MiniGate is a trademark of Semiconductor Components Industries, LLC (SCILLC).

ON Semiconductor and in are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at <a href="https://www.onsemi.com/site/pdf/Patent-Marking.pdf">www.onsemi.com/site/pdf/Patent-Marking.pdf</a>. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages.

Buyer is responsible for its products and applications using ON Semiconductor products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights nor the rights of others. ON Semiconductor products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor products for any such unintended or unauthorized application, Buyer shall indemnify and hold ON Semiconductor and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the design or manufacture of the part. ON Semiconductor is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## **PUBLICATION ORDERING INFORMATION**

#### LITERATURE FULFILLMENT:

Literature Distribution Center for ON Semiconductor 19521 E. 32nd Pkwy, Aurora, Colorado 80011 USA Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81–3–5817–1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative